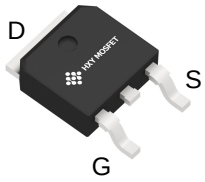
DMN6068LK3

N-Channel Enhancement Mode MOSFET

Description

The DMN6068LK3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

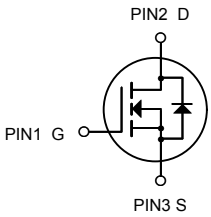


TO-252-2L
(TO-252-2(DPAK)

General Features

V_{DS} = 60V I_D =20 A

$R_{DS(ON)}$ < 32mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMN6068LK3	TO-252-2L(TO-252-2(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	20	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	10	A
I_{DM}	Pulsed Drain Current[2]	80	A
EAS	Single Pulse Avalanche Energy[3]	38	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	34.7	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60	-	-	V
Gate-Body Leakage Current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25℃	I_{DSS}	V_{DS} = 60V, V_{GS} = 0V	-	-	1	μA
	T_J=100℃			-	-	100	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.2	1.7	2.5	V
Drain-Source on-Resistance[4]		$R_{DS(on)}$	V_{GS} = 10V, I_D = 10A	-	25	32	mΩ
			V_{GS} = 4.5V, I_D = 5A	-	31.5	40	
Forward Transconductance[4]		g_{fs}	V_{DS} = 5V, I_D = 10A	-	15.5	-	S
Dynamic Characteristics[5]							
Input Capacitance		C_{iss}	V_{DS} = 30V, V_{GS} =0V, f =1MHz	-	1355	-	pF
Output Capacitance		C_{oss}		-	60	-	
Reverse Transfer Capacitance		C_{rss}		-	49	-	
Gate Resistance		R_G	f =1MHz	-	1.2	-	Ω
Switching Characteristics[5]							
Total Gate Charge		Q_g	V_{GS} = 10V, V_{DD} = 30V, I_D= 10A	-	22	-	nC
Gate-Source Charge		Q_{gs}		-	4.2	-	
Gate-Drain Charge		Q_{gd}		-	6.9	-	
Turn-on Delay Time		$t_{d(on)}$	V_{GS} =10V, V_{DD} = 30V, R_G = 3Ω, I_D= 10A	-	6.4	-	ns
Rise Time		t_r		-	15.3	-	
Turn-off Delay Time		$t_{d(off)}$		-	25	-	
Fall Time		t_f		-	7.6	-	
Body Diode Reverse Recovery Time		t_{rr}	I_F=10A, dI_F/dt=100A/μs	-	26	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}		-	45	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage[4]		V_{SD}	I_S = 10A, V_{GS} = 0V	-	-	1.2	V
Continuous Source Current	T_C=25℃	I_S	-	-	-	20	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C
2. The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.4mH, I_{AS}=14A
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

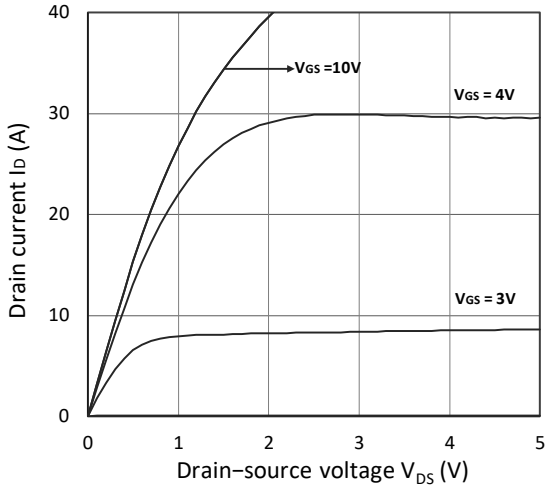


Figure 1. Output Characteristics

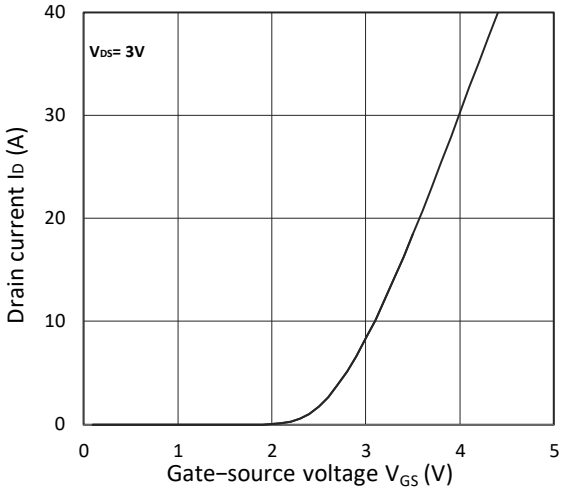


Figure 2. Transfer Characteristics

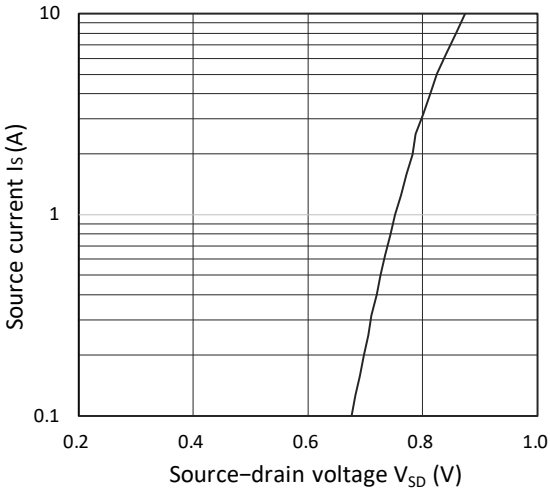


Figure 3. Forward Characteristics of Reverse

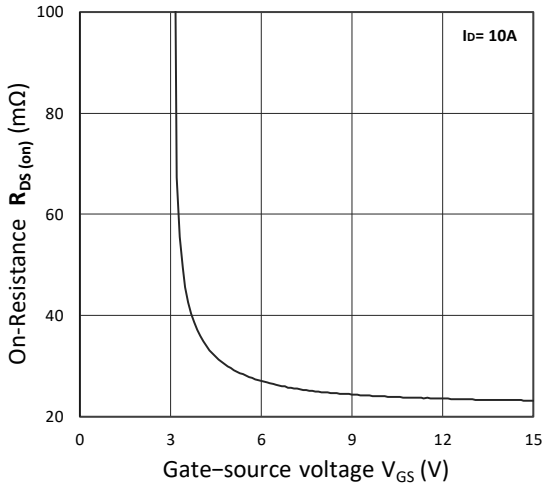


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

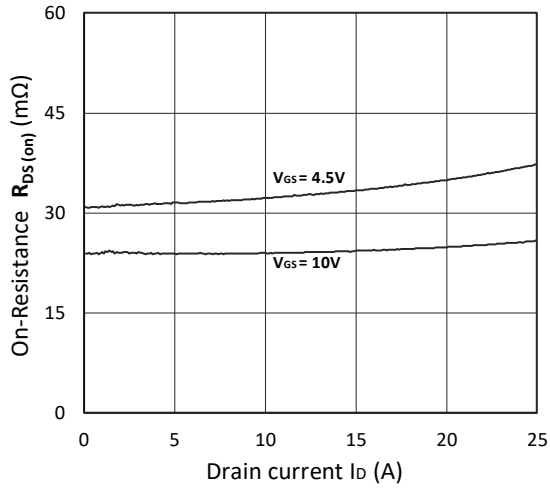


Figure 5. $R_{DS(ON)}$ vs. I_D

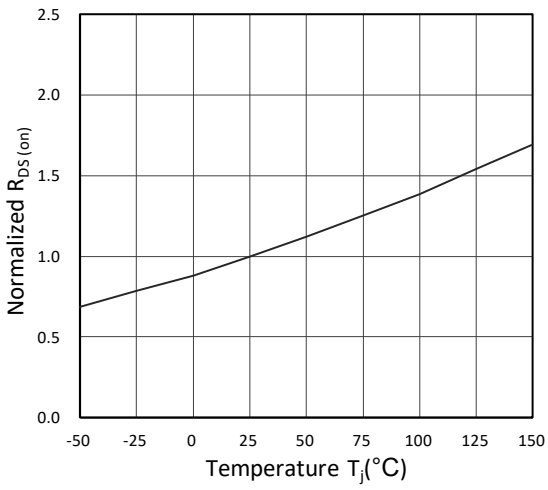


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

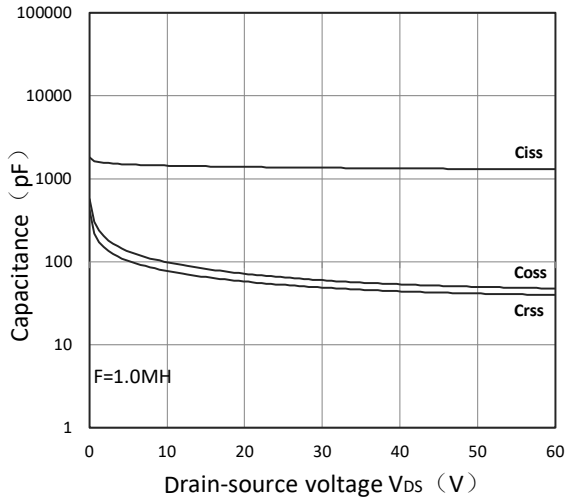


Figure 7. Capacitance Characteristics

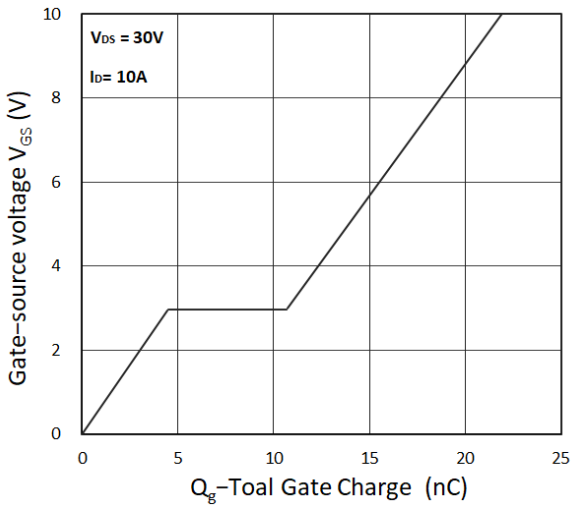


Figure 8. Gate Charge Characteristics

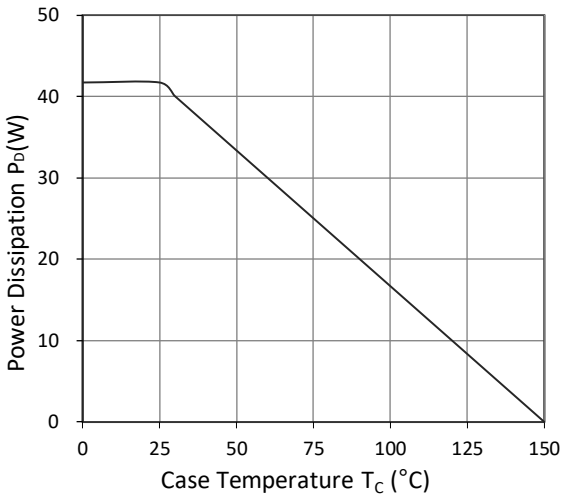


Figure 9. Power Dissipation

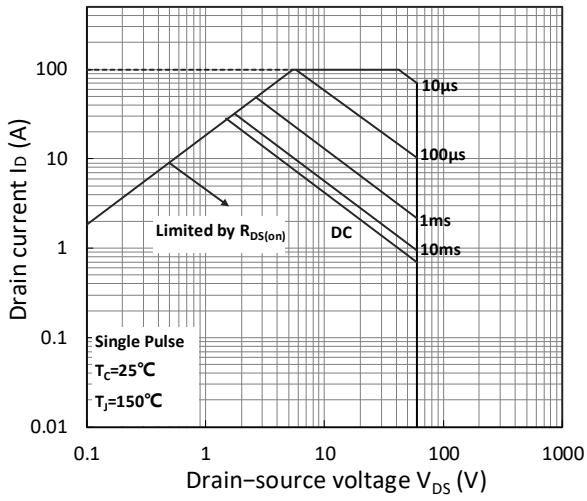


Figure10. Safe Operating Area

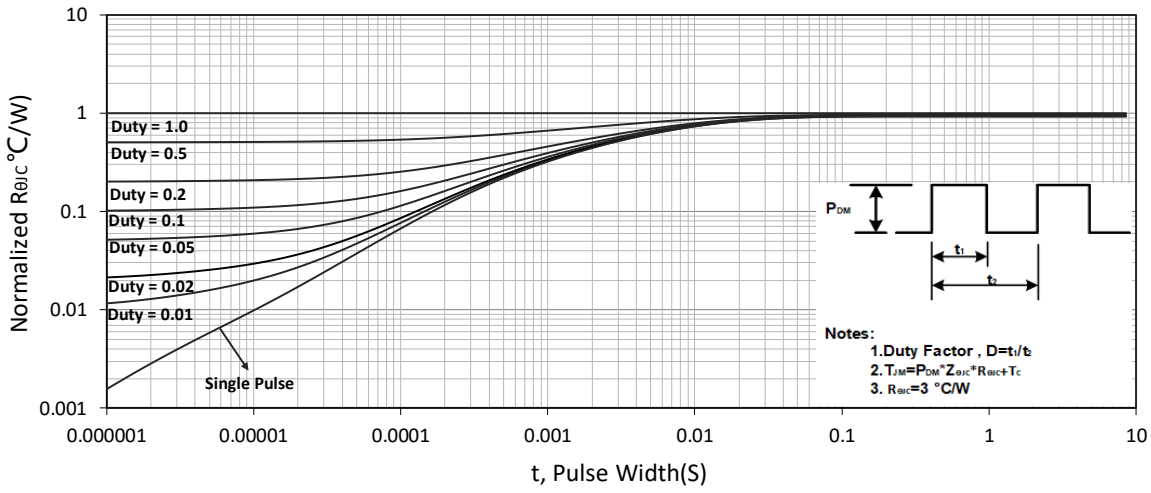
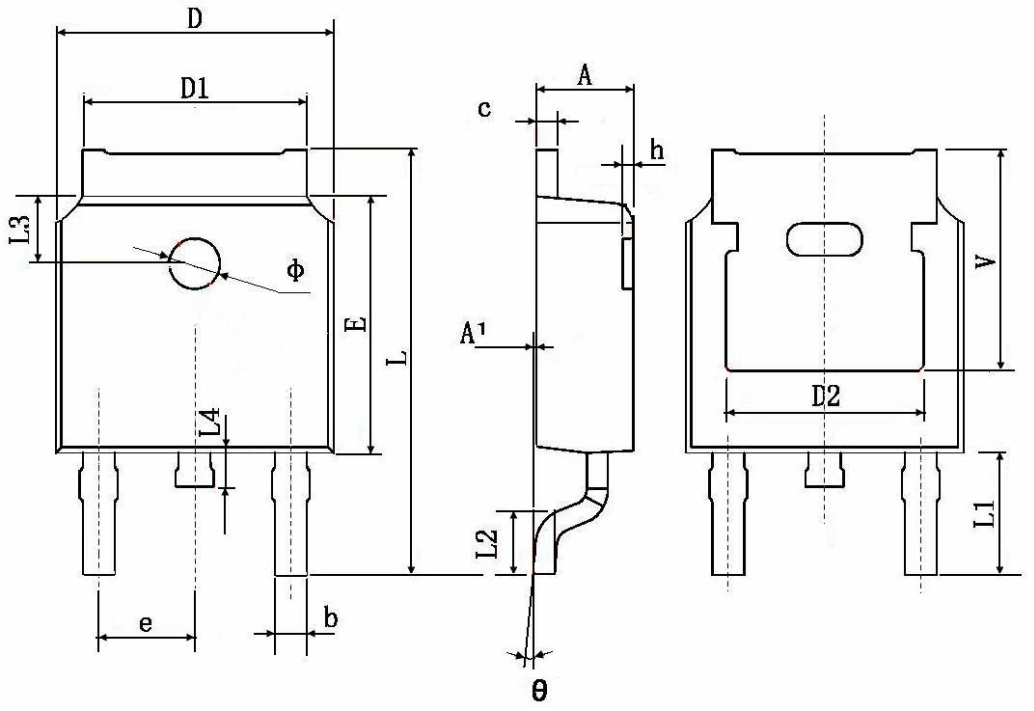


Figure 11. Normalized Maximum Transient Thermal Impedance

TO-252-2L(TO-252-2(DPAK)) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

Attention

■ Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.

■ HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

■ Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could
give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

Unikeyic Electronics

Global Electronic Components Distributor

Click to view pricing, inventory, delivery, and lifecycle information:

HXY MOSFET:

BZT52C13 HESDNC5VB1AF-B HT7150 HXY8205ES MAX487ESA SS5150B BZT52C3V3S HOPA2340UA PESD5V0S1BB MMBT3904T P6SMB200A SD15C SS10100 TPSMB100CA-VR TPSMB28A-VR DTC143ZE HAD8542ARZ HC4D20120A IRLML6246PBF HMCP602-I/SN SQJA04EP-T1_BE3 HC3D10170A HXY2101EI HXY2300MI P6SMB33CA SS1045 US2M HT7540-1 SS510C P6SMB36CA